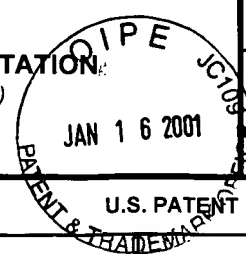


INFORMATION DISCLOSURE CITATION: (Use several sheets if necessary)				ATTY DOCKET NO. 990326		SERIAL NO. 09/319,699	
				Lippert et al.			
U.S. PATENT DOCUMENTS				FILING 19 July 1999		GROUP 2814	



*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>DA</i> A	4,855,614	12/89	Furukawa et al.	357	16	
B	5,177,025	1/93	Turner et al.	437	31	
C	5,360,986	11/94	Candelaria	257	183	
D	5,378,901	1/95	Nii	257	77	
E	5,387,807	2/95	Bayraktaroglu	257	197	

FOREIGN PATENT DOCUMENTS								
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION		
						YES	NO	
a	195 33 313 A1	3/97	Germany	H01L	29/16		✓	
b	36 30 282	3/88	Germany	H01L	29/86		✓	
c	38 23 249	1/89	Germany	H01L	29/267		✓	
d	43 01 333	7/94	Germany	H01L	21/331		✓	
e	0,552,561	7/92	EPO	H01L	21/331		✓	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
✓	aa	Prinz et al.: The Effects of Base Dopant Outdiffusion and Undoped Si-Ge Junction Spacer Layers in Si/Si-Ge/Si Heterojunction Bipolar Transistors; pp.42-44; IEEE Electron Device Letters, Vol. 12, No. 2, February 1991
✓	bb	Liefting et al.: Improved Device Performance by Multistep or Carbon Co-Implants; pages 50-55; IEEE Transactions on Electron Devices, Vol. 41, No. 1, January 1994

EXAMINER <i>Douglas Wills</i>	DATE CONSIDERED <i>19 Mar 01</i>
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

